

MELEC's PULSE BOOK

circuits and applications

first EDITION, June 2014

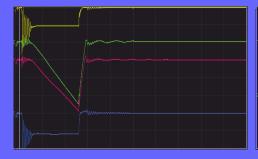
DC Pulse Power Controller for synchronized pulse applications:

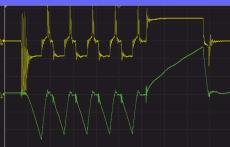
- HiPIMS
- Mid Frequency
- Pulsed Bias

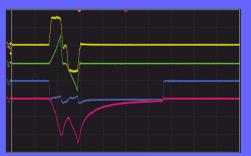
Superimposed Processes:

- HiPIMS + DC
- HiPIMS + MF
- HiPIMS + MF + Pulsed Bias









Company







Located in south Germany, MELEC produces and develops since 1998 DC-Pulse-Controller for plasma applications. With the experience of more than 15 years in power electronics and thin-film technology, MELEC sets standards in R&D and industrial applications.

MELEC products are utilized for the generations of highly ionized plasma discharges, often called "High Power Impulse Magnetron Sputtering" or HiPIMS. Our generators have become the standard tool for customers to meet their demanding requirements for pulsed plasma applications. They are designed fo the future, having great flexibility and process robustness in mind. The integrated Free-Pulse-Patter Generator (FPPG) makes it possible to develop, adjust and stabilize wide ranges of innovative processes.

Based on its international patents, MELEC is involved in various publications resulting from cooperation's with a large number of well-known research institutes and universities.

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MELEC's Know How Fits Customers Needs

Consulting

MELEC provides products for high performance pulse-power-applications but also plasma consulting for research and development of industrial applications worldwide.

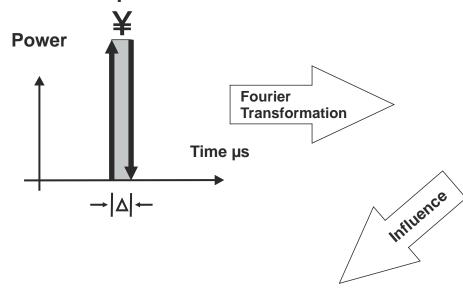
Our Mission

MELEC's SIPP-Technology (Superimposed Pulse Power-Technology) using HiPIMS (High Power Impulse Magnetron Sputtering) combined with DC, Mid-frequency or radio frequency 13.56 Mhz (bias) opens a new horizon in pulse plasma technology. The development of MELECs pulse power controller continues and is focused on advanced technology to create new additional features and advantages.

Our Quality Aspirations

MELEC is a synonymous for quality meeting a high level of expectations. Our goal is to be a reliable business base for our customers by providing and implementing innovative pulse-plasma-solutions centered around our SIPP Technology. We arrive at those solutions in close collaboration and ensure that solutions are sustainable and robust.

Our Philosophy About High Pulse Power Plasma Implementation



PULSE FUNCTION

Pulsing allows us to use high peak power while keeping the average power relatively low, making it easy on power grid demands while reaching technologically interesting plasma states.

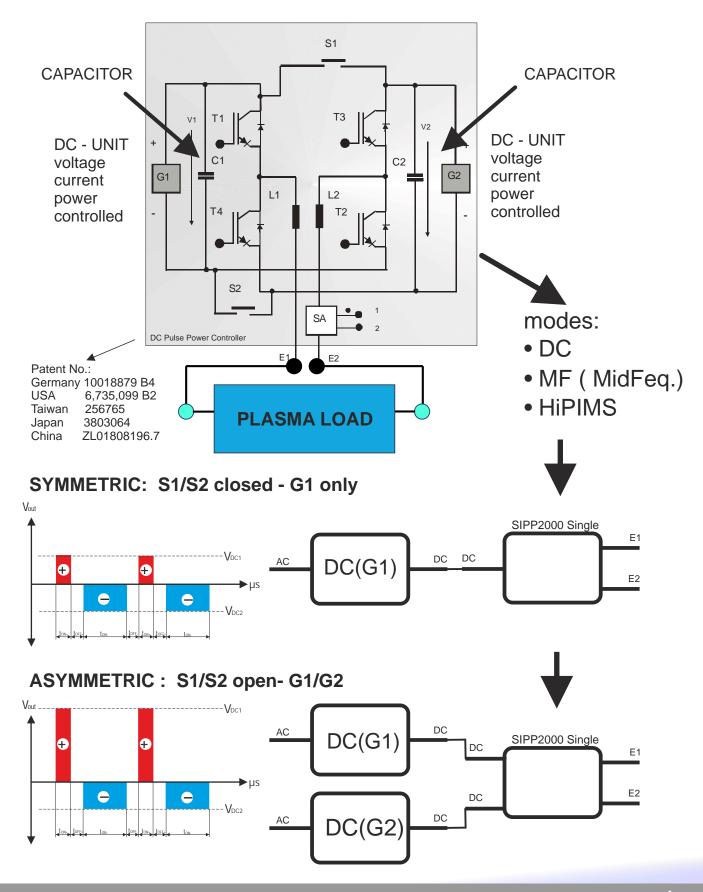
THIN FILM PROPERTIES

3



Advantages

Symmetric / Asymmetric bipolar pulse pattern



Single or Dual Magnetron applications

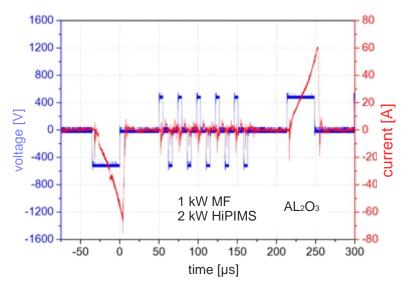
Applicable to CO – SPUTTERING (different target materials)

DC, unipolar, bipolar pulse patterns.

Pulse patterns are freely adjustable for both positive and negative pulse parameters through a graphic user interface of the interactive software.

MELEC's SIPP – Technology

- Highest deposition rate using HiPIMS combined with DC or Mid-Frequency so called SIPP – Technology Super Imposed Pulse Power Technology.
- Opens new horizons in pulsed plasma technology.
- Reducing of ARCING using pulse package mode instead of pure HiPIMS-mode only.
- Avoidance and prevention of poisoning using HiPIMS-BP combined with Mid-Frequency-BP



Superimposed bipolar HiPIMS (BP) and bipolar MF

Separation of metal and gas ions:

Synchronization or phase shift of pulsed bias voltage in relation to the HiPIMS Pulses – large power applications are ready utilizing to separate metal- and gas-ions treatment.

Synchronization or phase shift of pulsed radio frequency 13.56 MHz voltage in relation to the HiPIMS pulse. First tests were done with several 100 Watts on a laboratory PVD coater. This process is still under development.

Closed loop control

External pulse pattern input on each channel of the MELEC pulse power unit using for a closed loop control is possible. For example using an external OES-System, etc.

5

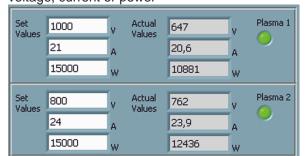


Software Modules of SIPP2000_USB Version using LabView

ADL 1 ON

ADL 2 OFF

DC 1, DC 2 controlled by setting values of voltage, current or power



Main Pulse Gen. Arc Control Status Config.

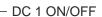
Features of software:

Full control of HiPIMS Pulse Unit

- Interactively configurable pulse waveform
- Saving and loading of pulse waveforms
- Freely adjustable arc management
- Monitoring of all status signals

Synchronized pulse generation output for external triggering of additional MF unit Full control of ADL GmbH DC-Units or alternatively PNCL DUAL® DC-Units

- Symmetric ON-OFF of two DC-Units
- Set point for voltage, current and power
- Reading of DC-Unit working parameters Industrial security functions
 - Control software runs on Windows XP or higher versions



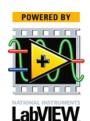
DC 2 ON/OFF

Pulse Channel A ON/OFF

Enable external pulse pattern Channel A

Pulse Channel B ON/OFF

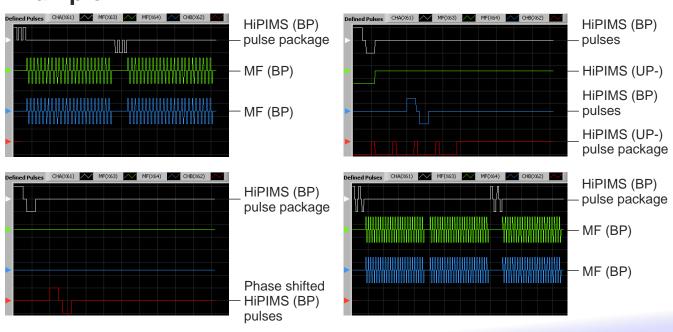
Enable external pulse pattern Channel B



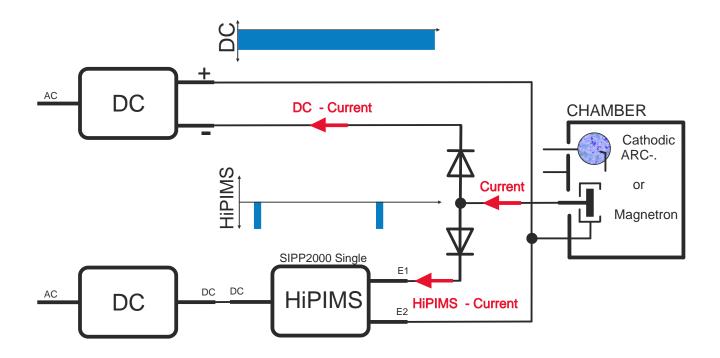
Example:

OK TO RUN

也



Superimposed DC / unipolar HiPIMS (UP) using Single Magnetron and Cathodic Arc

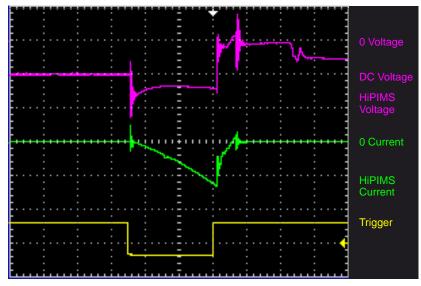


EXAMPLE OF APPLICATIONS:

- Large area coating on glass
- Retrofit of existing inline coating systems
- applicable using single magnetron or cathodic arc deposition

ADVANTAGES:

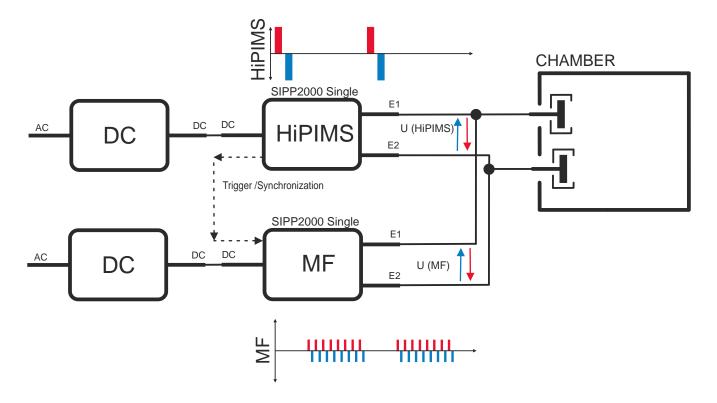
- Superimposed DC/HiPIMS(UP) with high depositions rate
- Smoother and denser films compared to DC sputtering
- low cost of retrofit
- easy control of single pulse or pulse packages



HiPIMS and DC



Superimposed bipolar HiPIMS (BP) / bipolar MidFreq. (MF)

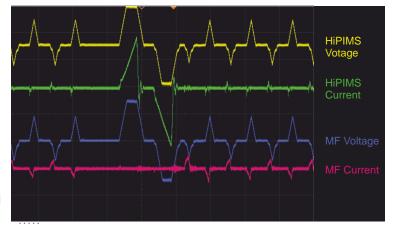


EXAMPLE OF APPLICATIONS:

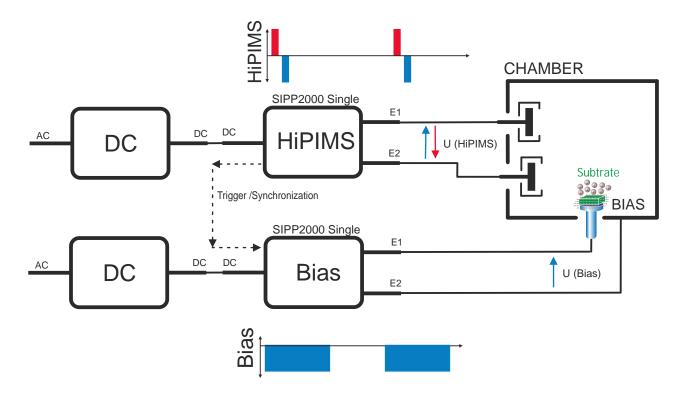
• Large area coating on glass

ADVANTAGES:

- Superimposed bipolar HiPIMS / bipolar Mid frequency (BP / MF) (MF-BP) with high depositions rate
- New pocess options
- Stable coating process
- Preventing of arcing and poisoning by control of bipolar Mid frequency (MF)



Bipolar HiPIMS (BP) and unipolar pulsed synchronized bias using conductive substrate

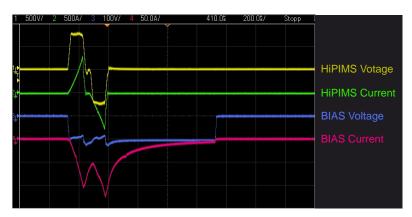


EXAMPLE OF APPLICATIONS:

- Hard and decorative coating using synchronized MF(UP) bias
- Synchronized or phase shifted to HiPIMS pulses

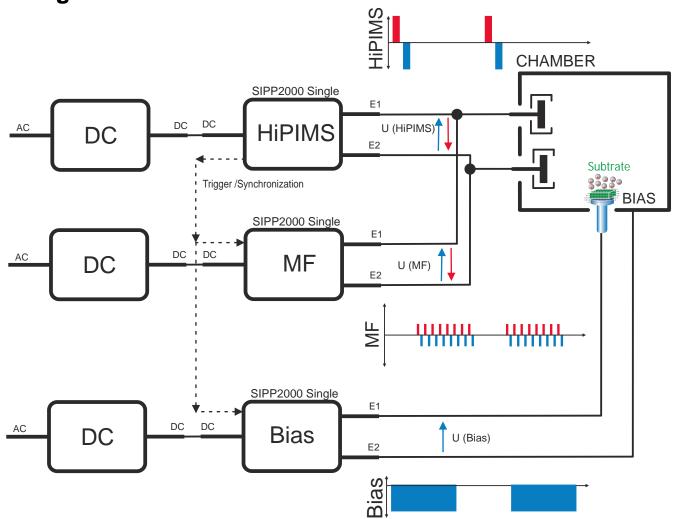
ADVANTAGES:

- Single- or Dual-Magnetron system application using conductive substrate allowes a variation of the process and high performance of thin film via improved micro-structure
- Separation of metal and gas ions





Superimposed bipolar HiPIMS (BP) / bipolar MidFreq. (MF) and unipolar MidFreq. (MF) synchronized pulsed BIAS using conductive substrate

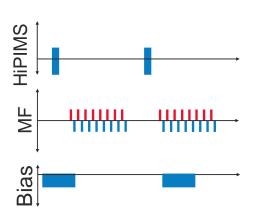


EXAMPLE OF APPLICATIONS:

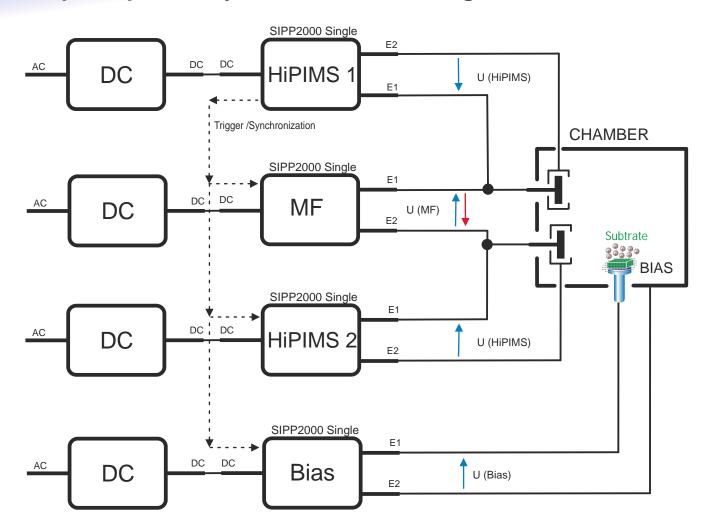
- Hard and decorative coating using synchronized MF(UP) bias
- Synchronized pulsed bias or phase shifted to HiPIMS pulses

ADVANTAGES:

- Single- or Dual-Magnetron system application using conductive substrate allowes a variation of the deposition process and high performance of thin film structures
- Superimposed HiPIMS(UP)/Mid Frequency (MF-BP) with high deposition rates
- New process options
- Stable coating process
- Preventing of arcing and poisoning by control of the Mid frequency parameters in bipolar (BP) mode
- Separation of metal and gas ions



Superimposed unipolar HiPIMS (UP) / bipolar MidFreq. (MF) and unipolar pulsed sychronized bias using conductiv substrate

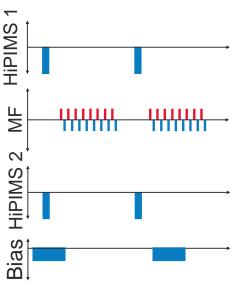


EXAMPLE OF APPLICATIONS:

- Hard and decorative coating using synchronized pulsed bias
- Synchronized pulsed bias or phase shifted to HiPIMS pulses

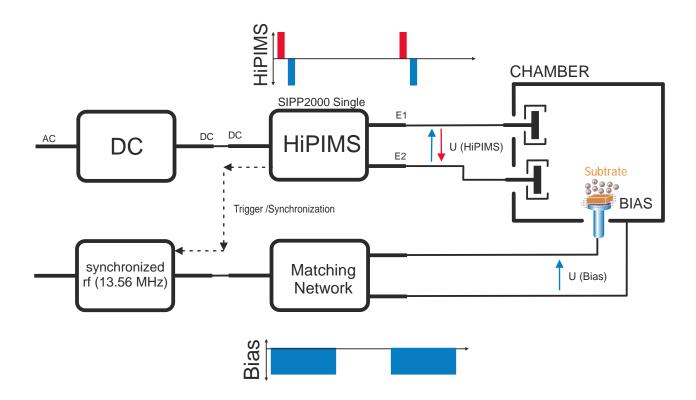
ADVANTAGES:

- Dual-Magnetron system application using conductive substrate allowes a variation of the process leading to high performance of thin film
- Superimposed HiPIMS / Mid Frequency (UP / MF) with high deposition rates
- New process options
- Stable coating process
- Preventing of arcing and poisoning by control of Mid Frequency (BP)
- Separation of metal and gas ions





Bipolar HiPIMS (BP) and synchronized pulsed radio frequency (13.56 MHz) (rf) bias using nonconductive substrate



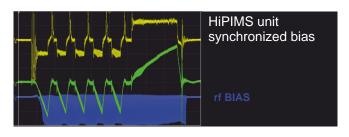
EXAMPLE OF APPLICATIONS:

- Co-sputtering with dual magnetron system using two different target materials (Al, Cr) in argon and nitrogen combined with synchronized pulsed rf (13.56 MHz) bias using a nonconductive substrate
- HiPIMS pulse waveforms fully sychronized with rf (13.56 MHz) bias pulse
- HiPIMS waveform phase shiftes with rf (13.56 MHz) bias pulse

ADVANTAGES:

- New process options
- Stable coating process
- Preventing of arcing and poisoning by control of HiPIMS (BP) using pulse packages for AI deposition and single pulses for Cr deposition
- Separation of metal and gas ions

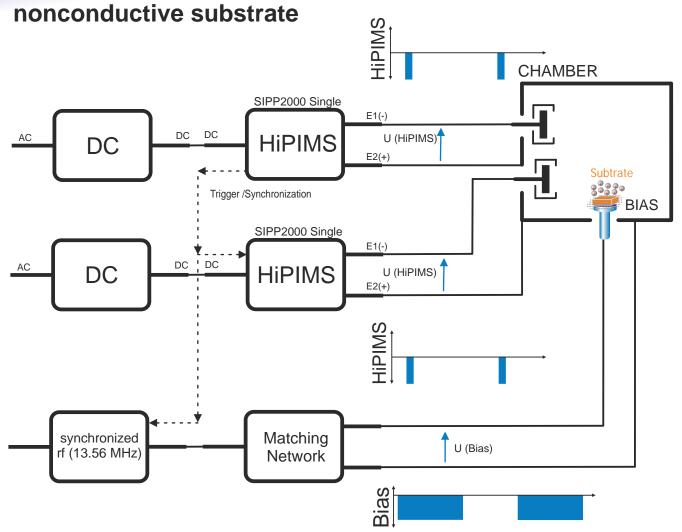






Patent Pending

Superimposed unipolar HiPIMS (UP) and synchronized pulsed radio frequency (13.56 MHz) (rf) bias using

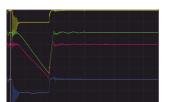


EXAMPLE OF APPLICATIONS:

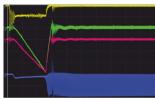
- Co-sputtering with two dual magnetron system with two different target materials (AI, Cr) using argon and nitrogen combined with synchronized pulsed rf (13.56 MHz) bias using nonconductive substrate
- HiPIMS pulse waveforms full sychronized with rf (13.56 MHz) bias pulse
- HiPIMS waveform phase shiftes with rf (13.56 MHz) bias pulse

ADVANTAGES:

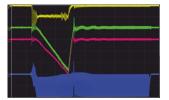
- New process options
- Stable coating process
- Preventing of arcing and poisoning by control of HiPIMS (BP) using pulse packages for Al
- Separation of metal and gas ions



HiPIMS without bias



HiPIMS unit pulse shifted synchronized pulsed rf bias



HiPIMS unit synchronized pulsed rf bias



10 kW

1000 kW (peak)

+/- 1000 V max. +/- 1000 A max.

UP+; UP-; BP

Ton */- 20 μs

Toff +/- 20 μs

(2 kHz)

Ton $^{+/-}$ 5 μs

Toff +/- 5 μs

Current pulse peak +/-100 A

(50 kHz)

 $T(n^{+/-})$ and $T_{off}^{+/-}$ 20 µs

T($n^{+/-}$ and Toff $^{+/-}$) 500 μs

...30_1000_S x 15 kW = 30 kW or 1x 30 kW

SIPP2000 Single Version PLASMA DC PULSE POWER CONTROLLER

SIPP2000USB-HiPIMS

HIPIMS/HPPMS

SIPP2000USB .

Pulse Output Power

Pulse Output Voltage

Pulse Output Current

Pulse Time Conditions

ON-TIMES +/-

OFF-TIMES +/-

MF (optional)

ON-TIMES +/-

MF (optional)

MF (optional)

OFF-TIMES +/-

HiPIMS / HPPMS

Frequency Conditions

Frequency Conditions

00010

10 kW



Features:

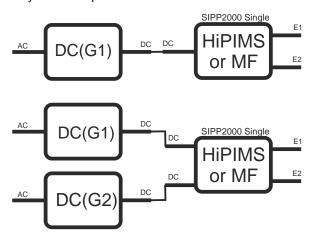
- Full control of MF Pulse Unit configured for 1 CH or 2 CH functionality
- Interactively configurable Pulse Waveform
- Saving and Loading of Pulse Waveforms
- Freely adjustable arc Management
- Monitoring of all status signals
- Synchronized pulse generation output for external triggering of additional MF unit
- Full control of ADL GmbH DC-Units or alternatively PNCL DUAL® DC-Units
- Set points for voltage, current and power
- Industrial security functions

SIPP2000USB-MF

MidFrequency SIPP2000USB	10_1000_S 10 kW	20_1000_S 2x 10 kW = 20 kW	30_1000_S 2x 15 kW = 30 kW or 1x 30 kW
Pulse Output Power	1000 kW (peak)		
Pulse Output Voltage	+/- 1000 V max.		
Pulse Output Current	+/- 500 A max.		
Pulse Time Conditions	UP+ ; UP- ; BP		
ON-TIMES +/-		Ton */- 5 μs	
OFF-TIMES +/-		Toff */- 5 µs	
MidFrequency Conditions	T6n* ⁴⁻ and Toff ⁴⁻) 20 μs Current pulse peak +/-100 A (50 kHz)		

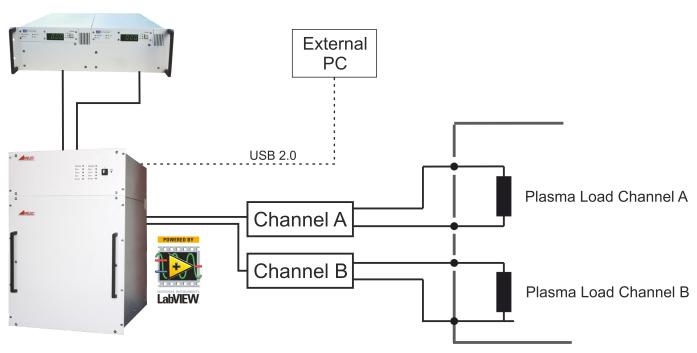
Possibilty:

Use one or two DC units for symmetric or asymmetric pulse mode



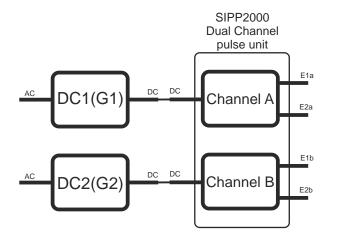
SIPP2000 Dual Version PLASMA DC PULSE POWER CONTROLLER

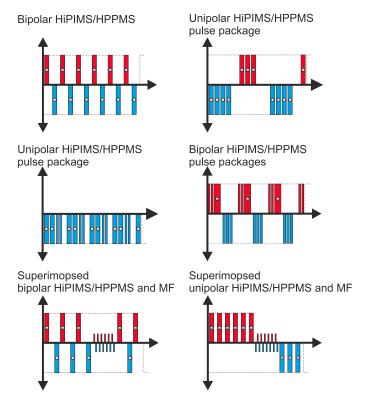
DC 1 DC 2



Features:

- Full control of two separated channels for HiPIMS, MF or Bias
- Synchronization of HiPIMS, Bias and MF
- Separated arc management for both channels
- Control of 2 DC units (2 x ADL GX or PNCL Dual)
- All parameters can be controlled via software
- Freely adjustable pulse pattern generator (FPPG)





Patent Pending



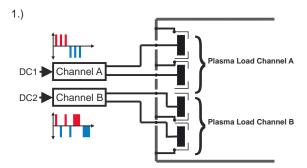


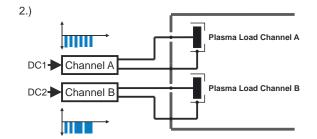
Source: Helmholtz-Zentrum Dresden-Rossendorf Germany

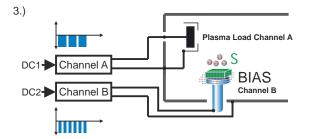
SIPP2000 DUAL

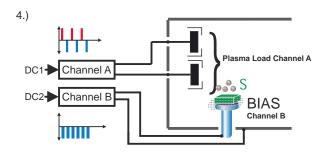
1x HiPIMS/HPPMS and 1x MF or 2x HiPIMS/HPPMS or 2x Mid Frequency(MF)	CHANNEL A 5 KW	CHANNEL B 5 KW	
Pulse Output Power (peak Power)	500 kW	500 kW	
Pulse Output Voltage	+/- 1000 V (max.)	+/- 1000 V (max.)	
Pulse Output Current	+/- 500 A (max.)	+/- 500 A (max.)	
Pulse Time Conditions	UP+ ; UP- ; BP	UP+; UP-; BP	
HiPIMS/HPPMS ON-TIMES +/-	T _{on} +/- 20 μs	T _{on} +/- 20 μs	
HiPIMS/HPPMS OFF-TIMES +/-	T _{off} +/- 20 μs	T _{off} +/- 20 μs	
HiPIMS/HPPMS Frequency Conditions	(off+/- and Toff+/-) 500 μs Current Pulse Peak +/-500 A (2 kHz)		
MF ON-TIMES +/-	Ton +/- 5 μs	Ton +/- 5 μs	
MF OFF-TIMES +/-	T _{off} ^{+/-} 5 μs	T _{off} ^{+/-} 5 μs	
MF Frequency Conditions	T(n * ^{/-} and T _{off} * ^{/-}) 20 μs Current Pulse Peak +/-100 A (50 kHz)		

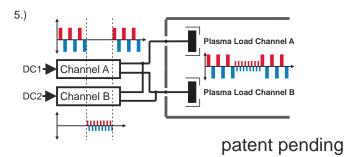
Applications...











DC Power Supply GS- and GX-Models, ADL GmbH



Туре		DC Output	
ADL GmbH GS Class			
GS15/1000	1000V	2,4 A	1,5 kW
GS15/1000	1000V	2,8 A	2,0 kW
GS15/1000	1000V	4,2 A	3,0 kW
ADL GmbH GX Class			
GX50/1000	1000V	10,0 A	5,0 kW
GX80/1000	1000V	16,0 A	8,0 kW
GX1000/1000	1000V	20,0 A	10,0 kW
GX150/1000	1000V	30,0 A	15,0 kW

DC Power Supply HX- Models, ADL GmbH



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Туре			
HX 150/1000	15 kW	1000 V	25 A
HX 200/1000	20 kW	1000 V	35 A
HX 250/1001	25 kW	1000 V	40 A
HX 300/1001	30 kW	1000 V	50 A

MELEC Measurement System



	Measurement System
MS-500-S	2 Channels (1 x 500 A, 1 x 1000 V)
MS-500-S-TB	2 Channels (1 x 500 A, 1 x 1000 V, 1x housing for Transducer Model)
MS-500-D	4 Channels (2 x 500 A, 2 x 1000 V)
MS-500-D-TB	4 Channels (2 x 500 A, 2 x 1000 V, 2x housing for Transducer Model)
MS-1000-S	2 Channels (1 x 1000 A, 1 x 1000 V)
MS-1000-S-TB	2 Channels (1 x 1000 A, 1 x 1000 V, 1x housing for Transducer Model)
MS-1000-D	4 Channels (2 x 1000 A, 2 x 1000 V)
MS-1000-D-TB	4 Channels (1 x 500 A, 1 x 1000 V, 2x housing for Transducer Model)





System Rack



Source: Materials Chemistry, RWTH / University Aachen, Prof. Jochen M. Schneider



Cabinet System with Dual Channel Pulse Unit set with a 4-Channel Measurement System

System Racks can be configurated to mount:

- SIPP2000 units
- DC units
- · Measurement applications
- Industrial personal computer
- etc.

Additional components for superimposed pulse applications, such as high power, high speed diodes for DC-superimposed pulses can be optionally added into the system rack.

Advantages:

- Easy to install, ready to use
- All Components mounted compact and safely

Further Applications:

Plasma CVD Plasma Nitriding Atmospheric Plasma Plasma Oxidation



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